

BG600F12LNP8

$$V_{CES} = 1200V \quad I_C = 600A$$

General Description

BYD IGBT Power Module BG600F12LNP8 provides low switching loss as well as high short circuit capability, which introduce the advanced FS IGBT chip and ultra fast & soft recovery anti-parallel FRD to improved connection, it is able to take on a perfect performance in various applications up to 16KHz.

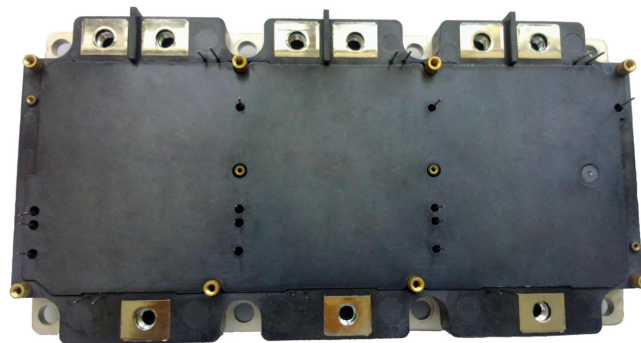
比亚迪IGBT功率模块BG600F12LNP8提供低损和高短路能力, 内含先进的平面栅场终止技术IGBT和超快速软恢复二极管芯片, 在不超过16KHZ频率的应用中表现出优良的性能

Features

- Full bridge module
全桥模块
- High short circuit withstand capability
高短路能力
- 1200V planar&field stop technology
1200V 平面栅场终止技术
- Ultra low conduction and switching loss
低导通和开关损耗
- Including ultra fast & soft recovery anti-parallel FRD
反并联超快速软恢复二极管

Applications

- AC motor control
交流马达控制
- Inverters
逆变器
- Servo
伺服电机
- Maximum applied voltage platform: 750V
最高支持750电压平台





Characteristic Values

Parameter	Symb	Conditions	Temperature	Value			Unit
Absolute Maximum Ratings/ 最大额定值							
Collector-emitter voltage 集电极—发射极电压	V _{CES}	V _{GE} =0V	T _{vj} =25℃	1200			V
Continuous collector current 连续集电极直流电流	I _{cnom}	—	T _F =65℃	580			A
	I _C	—	—	600			
Peak collector current 集电极峰值电流	I _{CRM}	I _{CRM} =2×I _C	—	1200			A
Gate-emitter voltage 栅极-发射极电压	V _{GES}	—	—	+/-20			V
IGBT short circuit SOA IGBT 短路安全工作区	t _{psc}	V _{CC} =800V, V _{CEM} ≤1200V, V _{GE} ≤15V	T _{vj} ≤150℃	10			us
Junction temperature 结温	T _{vj}	—	—	-40~175			℃
Storage temperature range 存储温度	T _{stg}	—	—	-40~150			℃
Diode DC forward current 二极管直流正向电流	I _{Fnom}	—	T _F =65℃	580			A
	I _F	—	—	600			A
Isolation voltage 绝缘电压	V _{isol}	AC,t=1min, f=50Hz	—	3000			V
Total power dissipation 耗散功率	P _{tot}	per switch (IGBT)	T _C = 25℃	1744			W
IGBT Characteristics IGBT 特性							
IGBT				Min.	Typ.	Max.	Unit
Collector-emitter breakdown voltage 集电极—发射极击穿电压	V _{(BR)CES}	V _{GE} =0V, I _C =3mA	T _{vj} =25℃	1200			V
Gate-emitter threshold voltage 栅极-发射极阈值电压	V _{GE(th)}	I _C =24mA, V _{CE} =V _{GE}	T _{vj} =25℃	5.0	6.0	7.0	V
Collector-emitter cut-off current 集电极-发射极截止电流	I _{CES}	V _{CE} =1200V, V _{GE} =0V	T _{vj} =25℃	—	—	1.2	mA
Gate-emitter leakage current 栅极-发射极漏电流	I _{GES}	V _{CE} =0V, V _{GE} =20V	T _{vj} =25℃			600	nA
Collector-emitter saturation voltage 集电极-发射极饱和电压	V _{CE(sat)}	I _C =600A, V _{GE} =15V	T _{vj} =25℃	1.8	—	2.9	V
			T _{vj} =150℃	—	2.20	—	V
Integrated gate resistor 内部栅极电阻	R _{Gint}	—	T _{vj} =25℃	—	0.9	—	Ω



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Parameter	Symbol	Conditions	Temperature	Min.	Typ.	Max.	Unit
IGBT Characteristics/ IGBT 特性							
Input capacitance 输入电容	C _{ies}	V _{CE} =25V, V _{GE} =0V, f=1MHz	—	—	23.8	—	nF
Reverse transfer capacitance 反向传输电容	C _{res}		—	—	1.1	—	nF
Turn-on delay time 开通延迟时间	t _{d(on)}	V _{CC} =600V I _c =600A, R _{Gon} =3.3Ω, R _{Goff} =5.0Ω, V _{GEon} =+15V, V _{GEoff} =-8V, L _S =30nH	T _{vj} =25°C	—	189	—	ns
Rise time 上升时间	t _r		T _{vj} =125°C	—	200	—	ns
			T _{vj} =150°C	—	204	—	ns
			T _{vj} =25°C	—	162	—	ns
Turn-off delay time 关断延迟时间	t _{d(off)}		T _{vj} =125°C	—	166	—	ns
			T _{vj} =150°C	—	168	—	ns
			T _{vj} =25°C	—	652	—	ns
Fall time 下降时间	t _f		T _{vj} =125°C	—	710	—	ns
			T _{vj} =150°C	—	744	—	ns
			T _{vj} =25°C	—	58	—	ns
Energy dissipation during turn-on time 开通损耗	E _{on}		T _{vj} =125°C	—	166	—	ns
			T _{vj} =150°C	—	200	—	ns
			T _{vj} =25°C	—	100	—	mJ
Energy dissipation during turn-off time 关断损耗	E _{off}		T _{vj} =125°C	—	110	—	mJ
			T _{vj} =150°C	—	118	—	mJ
			T _{vj} =25°C	—	42	—	mJ
Diode Characteristics/ 二极管特征值							
Forward voltage 正向电压	V _F	I _F =600A	T _{vj} =25	—	2.05	—	V
			T _{vj} =125°C	—	2.08	—	V
			T _{vj} =150°C	—	2.02	—	V
Peak reverse recovery current 反向恢复峰值电流	I _{RR}	I _F =600A, V _R =600V, R _{Gon} =3.3Ω	T _{vj} =25°C	—	111	—	A
			T _{vj} =125°C	—	151	—	A
			T _{vj} =150°C	—	165	—	A
Recovered charge 恢复电荷	Q _r		T _{vj} =25°C	—	33	—	uC
			T _{vj} =125°C	—	65	—	uC
			T _{vj} =150°C	—	75	—	uC
Reverse recovery energy 反向恢复能量	E _{rec}		T _{vj} =25°C	—	14	—	mJ
			T _{vj} =125°C	—	27	—	mJ
			T _{vj} =150°C	—	31	—	mJ



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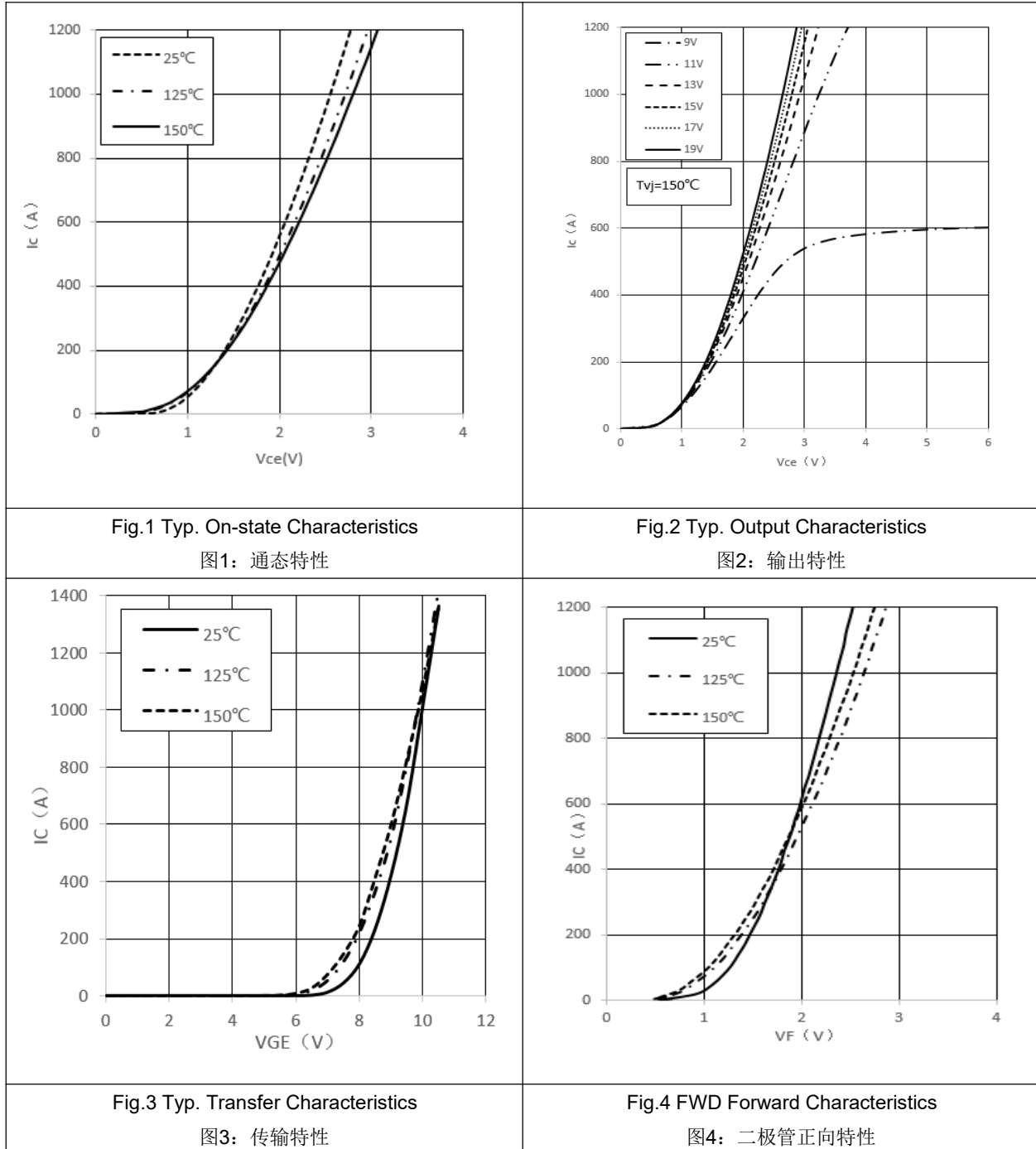
Thermal-Mechanical Specifications							
Thermal resistance junction to coolant 结到冷却液热阻	R _{th(j-f)}		IGBT	—	0.086	—	K/W
	R _{th(j-f)}		FRD	—	0.148	—	K/W
Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
Module Characteristics/ 模块特性							
Dimensions 尺寸	L x W x H	Typical , see outline drawing		217.1×113.4×38.0			mm
Clearance distance in air 空气间隙	da	according to IEC 60664-1 and EN 50124-1	Term. to base:	—	12	—	mm
			Term. to term:	6	—	—	
Surface creepage distance 爬电距离	ds	according to IEC 60664-1and EN 50124-1	Term. to base:	15	—	—	mm
			Term. to term:	—	12	—	
Mass 重量	m	—	—	—	1676	—	g
Pressure drop in cooling circuit 在冷却液中的压差	ΔP	Δv /Δt=12L/min, T=25℃ ,cooling fluid=50% water/50% ethylenglycol		—	10	—	KPa
Maximum pressure in cooling circuit 冷却循环中的最大压力	P	—		—	250	—	KPa
Stray inductance module 杂散电感	L _{sce}	—		—	18	—	nH
Module lead resistance, terminals – chip 模块引线电阻, 端子—芯片	R _{CC'+EE'}	—		—	0.75	—	mΩ
Mounting torque 安装扭矩	M	Screw M6-mounting according to valid application note		3.0	—	4.5	Nm
Terminal connection torque 端子连接扭矩	M	Screw M6-mounting according to valid application note		3.0	—	4.5	Nm
NTC-Thermistor Characteristic Values/ 热敏电阻特性							
Rated resistance 额定阻值	R ₂₅	T _C =25℃		—	5.0	—	KΩ
Deviation of R100 R100 偏差	ΔR/R	T _C =100℃, R ₁₀₀ =493Ω		-5	—	5	%
Power dissipation 耗散功率	P ₂₅	T _C =25℃		—	—	20.0	mW
B-value B-值	B _{25/50}	R ₂ =R ₂₅ exp[B _{25/50} (1/T ₂ -1/(298.15K))]		—	3375	—	K
B-value B-值	B _{25/80}	R ₂ =R ₂₅ exp[B _{25/80} (1/T ₂ -1/(298.15K))]		—	3411	—	K
B-value B-值	B _{25/100}	R ₂ =R ₂₅ exp[B _{25/100} (1/T ₂ -1/(298.15K))]		—	3433	—	K



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Thermal and mechanical properties according to IEC 60747 – 15, Specification according to the valid application note. 热和机械特性
参考 IEC 60747 – 15

Characterization Curves



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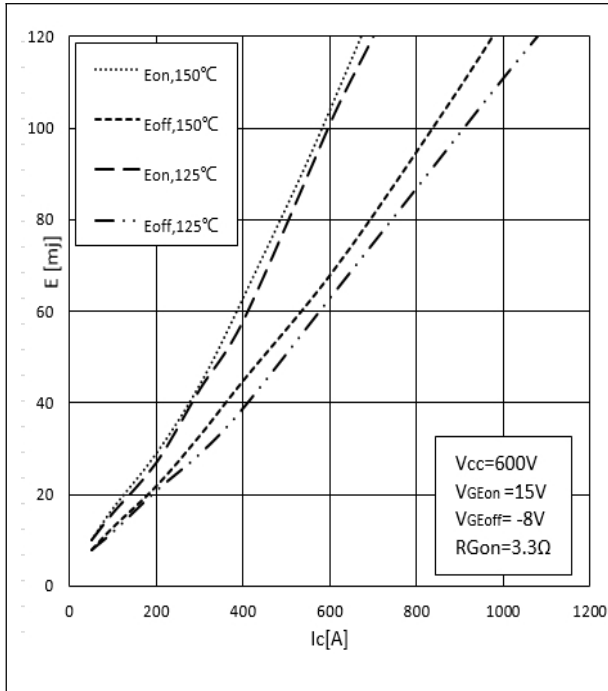


Fig.5: Switching Loss vs. Collector Current

图5: 开关损耗与集电极电流关系

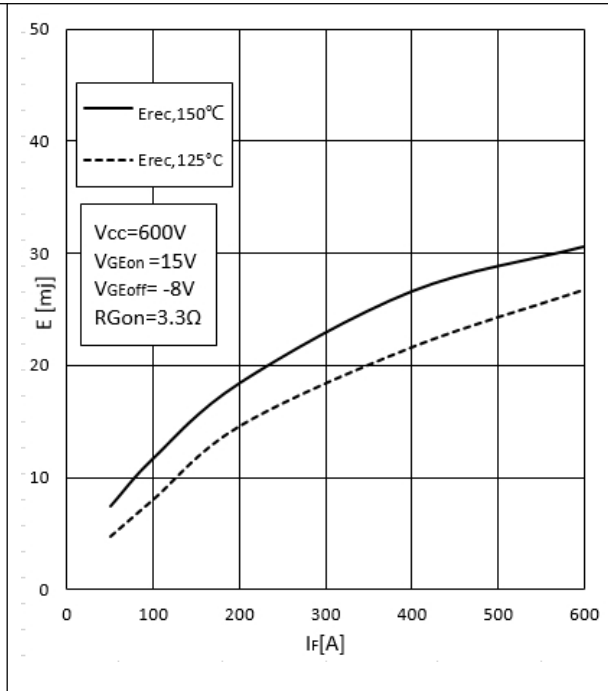


Fig.6: Reverse recovery Energy

图6: 反向恢复损耗

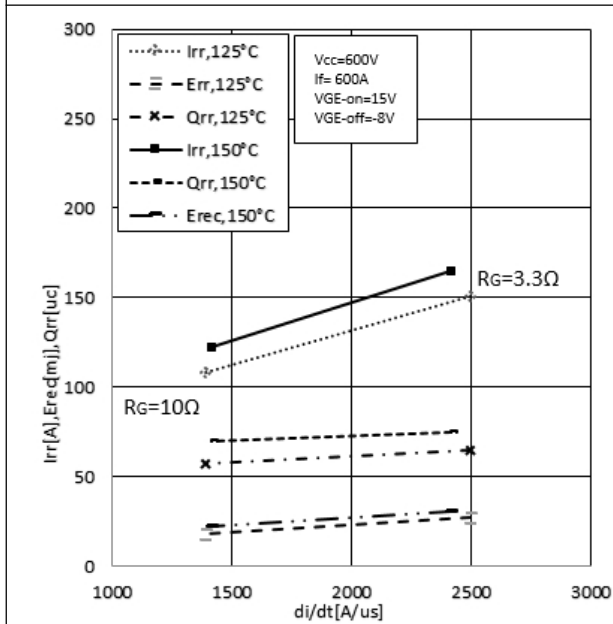


Fig.7 Typ. Reverse Recovery Characteristics vs. di/dt

图7: 反向恢复特性与di/dt关系

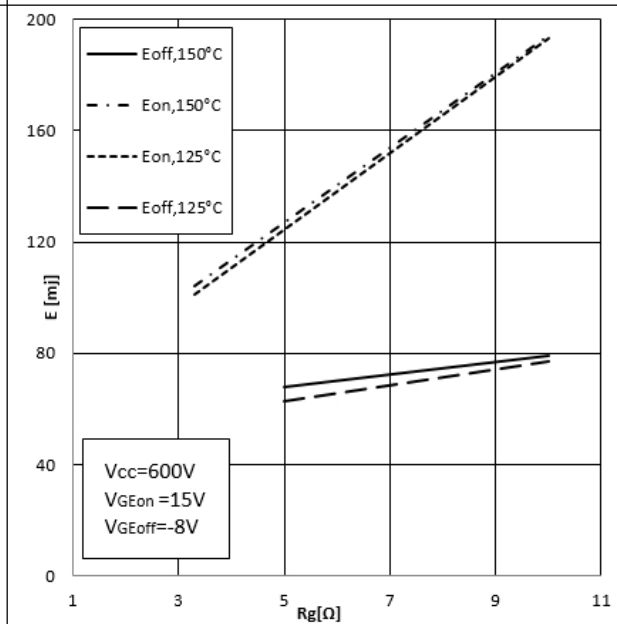


Fig.8: Switching Loss vs. Gate Resistor

图8: 开关损耗与门极电阻关系



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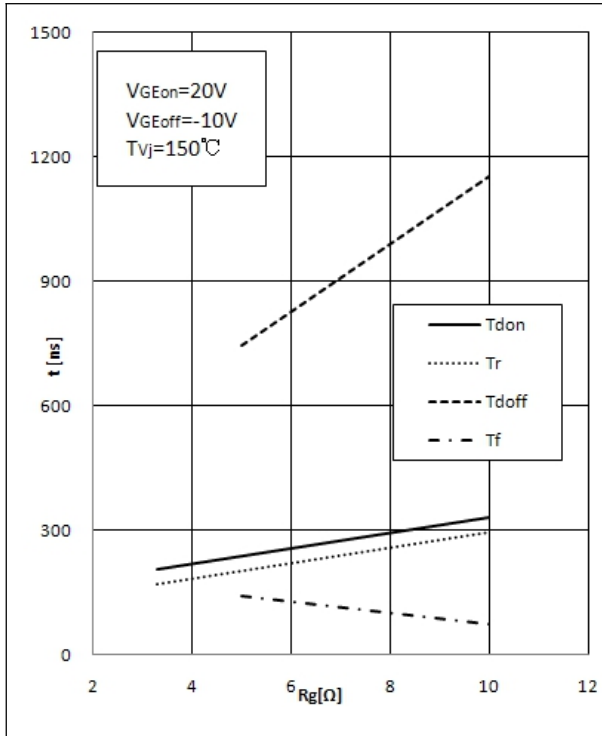


Fig.9: Switching Times vs. Gate Resistor

图9: 开关时间与门极电阻关系

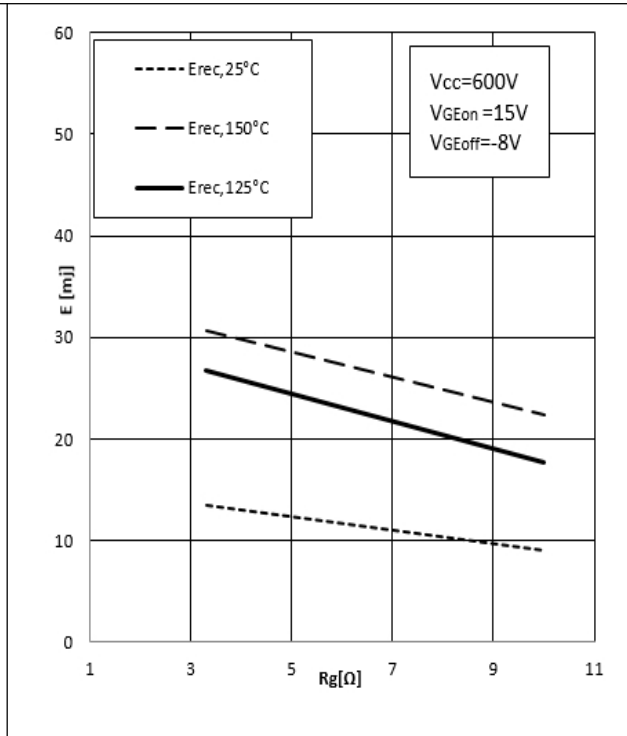


Fig.10: Reverse recovery Energy vs. Gate Resistor

图10: 反向恢复损耗与门极电阻关系

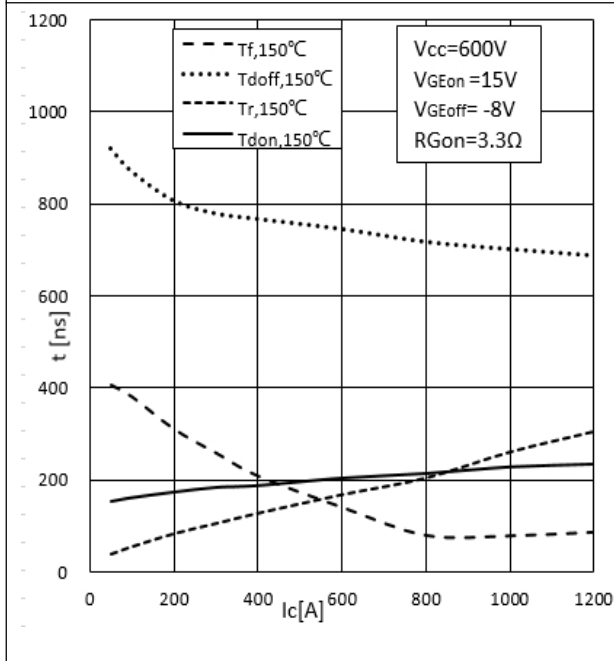


Fig.11: Switching Times vs. IC

图11: 开关时间与集电极电流关系

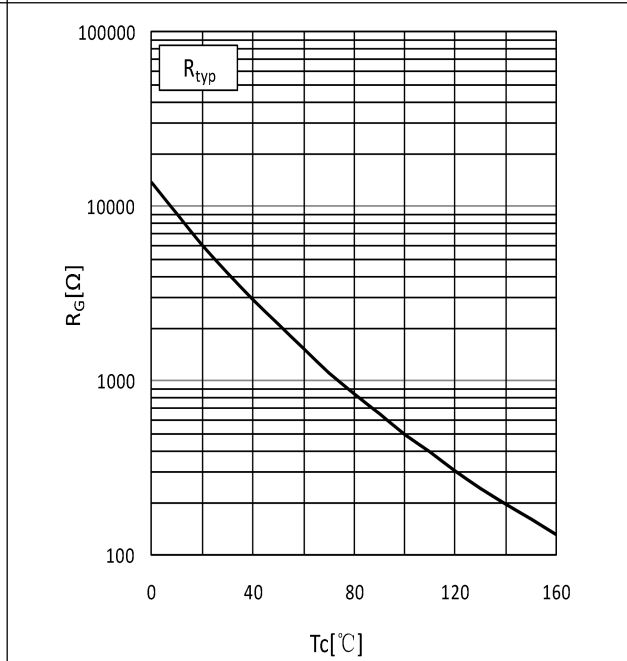


Fig.12 Typ. NTC-Temperature Characteristics

图12: NTC 热特性

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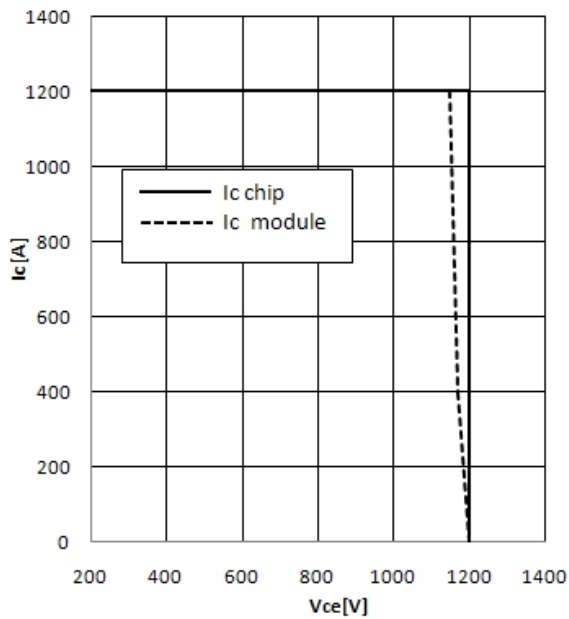


Fig.13: Reverse Bias Safe Operating Area

图13: 反偏安全工作区

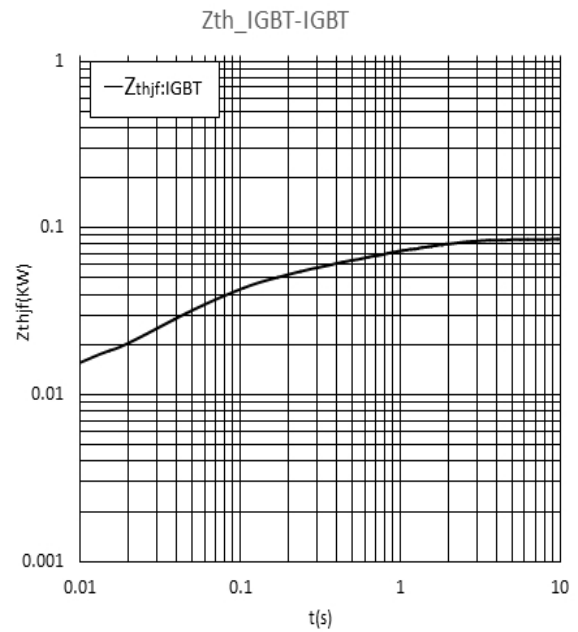


Fig.14: Typ. transient thermal impedance (IGBT) Z_{thJF}

IGBT (K/W)

图14: 典型的瞬态热阻抗 (IGBT) Z_{thJF} IGBT (K/W)

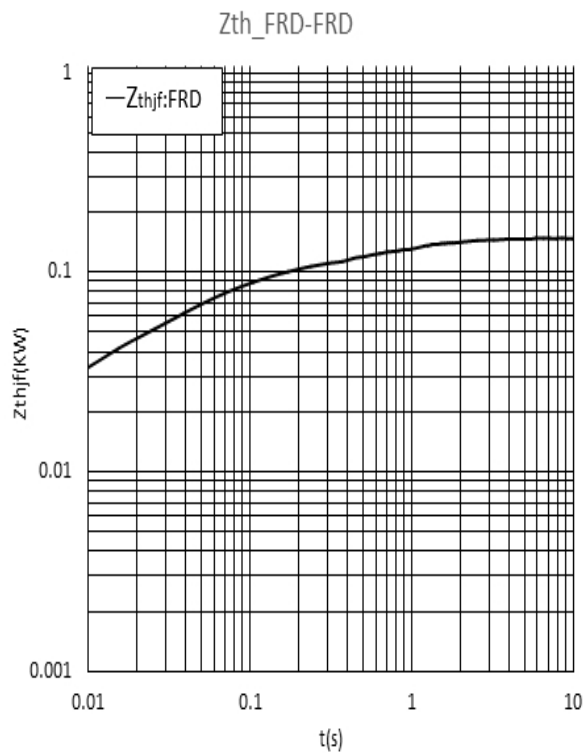


Fig.15: Typ. transient thermal impedance (FRD) Z_{thJF}

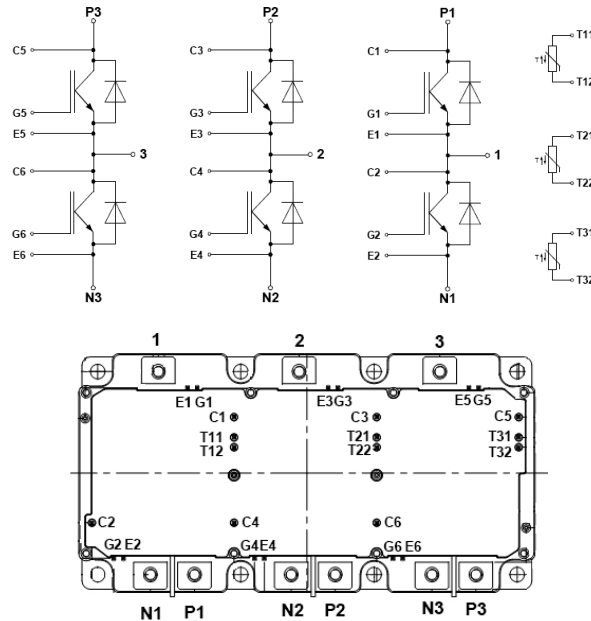
FRD (K/W)



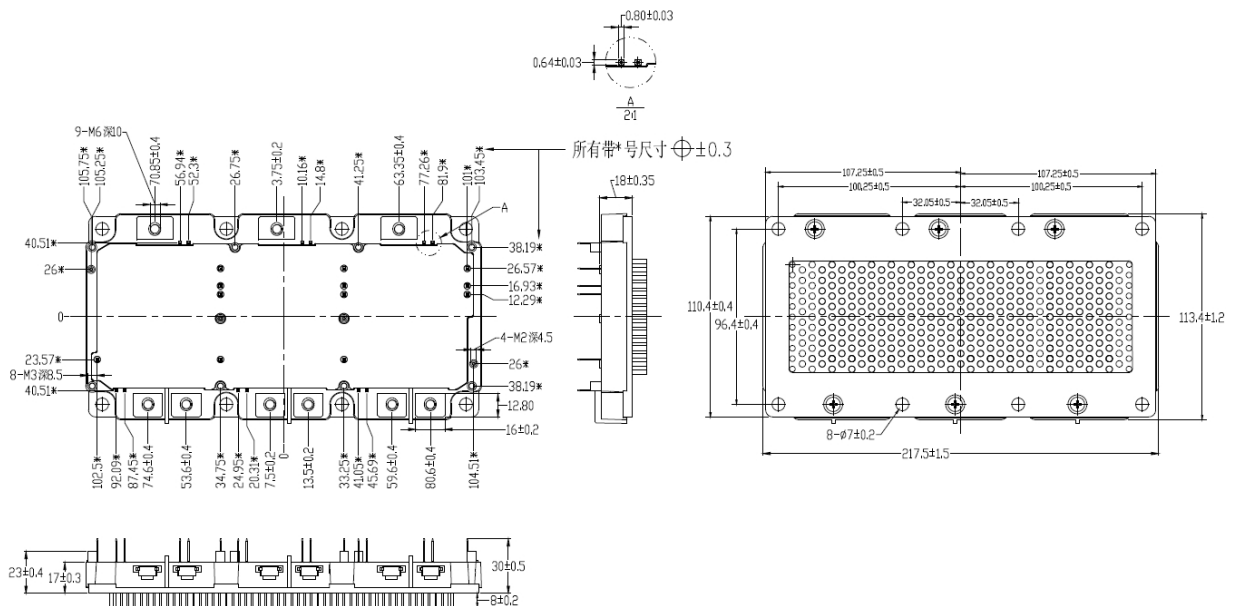
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图15: 典型的瞬态热阻抗(FRD) Z_{thJF} FRD(K/W)

Circuit Diagram



Package Outlines





Attached (recommended torque and screw):

Terminal Torque(M6): pre-tightening torque 0.5 N.m and final torque 3.0-4.5 N·m

端子扭矩(M6)预紧扭矩0.5 N.m, 最终扭矩3.0-4.5 N·m

Mounting Torque(M3):0.5-1.0 N·m

安装扭矩(M3): 0.5-1.0 N·m

For the 1.0mm thickness shielding plate mounting, we suggest you use the M2x5 screws

对于1.0mm厚度的屏蔽板安装, 建议使用M2X5的螺钉。

Attention

1. When installing the module, please wear an electrostatic bracelet to prevent the gate breakdown and the imbalance power may damage the internal chip, even to damage the module.

当您安装模块时, 请佩戴静电手环防止栅极被击穿, 静电可能会破坏芯片, 甚至损坏模块。

2. This is an electrostatic sensitive device, please observe the international standard IEC 60747-1, chap. IX.

这是静电敏感器件, 请遵循国际标准 IEC 60747-1, chap. IX。

Restrictions on Product Use

产品应用的限制

- The information contained herein is subject to change without notice.

此处包含的信息如有变更, 不另通知。

- **BYD Semiconductor Company Limited** exerts the greatest possible effort to ensure high quality and reliability. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing products, to comply with the standards of safety in making a safe design for the entire system, including redundancy, fire-prevention measures, and malfunction prevention, to prevent any accidents, fires, or community damage that may ensue. In developing your designs, please ensure that products are used within specified operating ranges as set forth in the most recent products specifications.



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